6. Parameters of parasitic devices

6.1 : Parasitic resistances:

6.1.1 : Salicide areas:

RESISTANCES	UNIT	SLOW	TYP.	FAST
N-Well Sheet Res.(Field)	Kohm/sq	1.2	0.7	0.20
N+ Sheet Res, width = 0.22 um	Ohm/sq	15.0	6	1.0
N+ Sheet Res, width >= 0.5 um	Ohm/sq	10.0	6	1.0
P+ Sheet Res, width = 0.22 um	Ohm/sq	15.0	6	1.0
P+ Sheet Res, width >= 0.5 um	Ohm/sq	10.0	6	1.0
Poly without N+ or P+ S/D implants:				
Poly Sheet Res, Width = 0.15 µm	Ohm/sq	15.0	6	1.0
Poly Sheet Res, Width >= 0.36 µm	Ohm/sq	10.0	6	1.0
N+ Poly Sheet Res (Poly with N+ S/D implant)	Ohm/sq	15.0	6	1.0
P+ Poly Sheet Res (Poly with P+ S/D implant)	Ohm/sq	15.0	6	1.0

6.1.2 : Non salicide areas (using blocking layer):

RESISTANCES	UNIT	SLOW	TYP.	FAST
N-Well Sheet Res.(Field)	Kohm/sq	1.2	0.7	0.2
N+ Sheet Res.	Ohm/sq	135	105	75
P+ Sheet Res.	Ohm/sq	170	130	90

POLY RESISTANCES (used as analog resistors)	UNIT	SLOW	TYP.	FAST
N+ Poly Sheet Res(Poly with N+ S/D implant)	Ohm/sq	800	1000	1200
Poly Sheet Res (Poly with CRES)	Ohm/sq	270	235	200